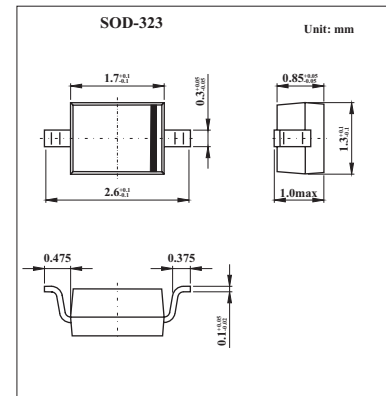


Silicon Epitaxial Planar Diode

1SV239

■ Features

- Ultra Low Series Resistance: $r_s = 0.44 \Omega$ (Typ.)
- Useful for small size Set

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	15	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1 \mu\text{A}$	15			V
Reverse Current	I_R	$V_R = 15\text{V}$			3	nA
Capacitance	C_{2V}	$f = 1\text{MHz}; V_R = 2\text{V}$	3.8	4.25	4.7	pF
	C_{10V}	$f = 1\text{MHz}; V_R = 10\text{V}$	1.5	1.75	2.0	
Capacitance Ratio	C_{2V}/C_{10V}		2	2.4		
Series Resistance	r_s	$V_R = 1\text{V}, f = 470\text{MHz}$		0.44	0.6	Ω

■ Marking

Marking	TC
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